

PerFET™ Power Transistor

FEATURES

- Excellent FOM
- AEC-Q101 Qualified
- Wettable Flank leads for Enhanced AOI
- 100% UIS and R_g tested
- 175°C Operating Junction Temperature
- RoHS Compliant
- Halogen-Free

PRODUCT SUMMARY		
PARAMETER	VALUE	UNIT
V _{DS}	40	V
R _{DS(on)} (max)	V _{GS} = 10V	1.9
	V _{GS} = 7V	2.3
Q _g	V _{GS} = 10V	nC

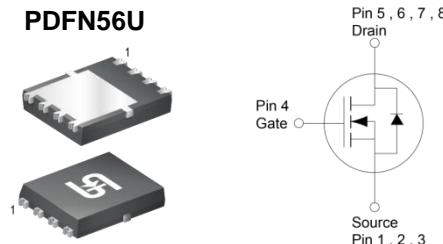
APPLICATIONS

- Automotive Applications
- Solenoid and Motor Drivers
- DC-DC Converters



✓
RoHS
COMPLIANT

HALOGEN
FREE



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current, Silicon limited	I _D	214	A
Continuous Drain Current (Note 1)	I _D	100	A
		100	
		30	
		400	
Pulsed Drain Current (Note 2)	I _{DM}	41.9	A
Single Pulse Avalanche Current (Note 3)	I _{AS}	262.9	mJ
Total Power Dissipation	P _D	150	W
		50	
Operating Junction and Storage Temperature Range	T _J , T _{STG}	- 55 to +175	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	R _{θJC}	1	°C/W
Thermal Resistance – Junction to Ambient (Note 4)	R _{θJA}	50	°C/W

NOTE:

1. Package current limit.
2. Pulse Width ≤ 100μs.
3. L = 0.3mH, V_{GS} = 10V, R_G = 25Ω, Starting T_J = 25°C.
4. Device on a PCB FR4 with 1 in² (single layer, 2 oz thick) copper area for drain connection.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$	BV_{DSS}	40	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	$V_{GS(\text{TH})}$	2.4	3	3.6	V
Gate-Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Drain-Source Leakage Current	$V_{GS} = 0\text{V}, V_{DS} = 40\text{V}$	I_{DSS}	--	--	1	μA
	$V_{GS} = 0\text{V}, V_{DS} = 40\text{V}$ $T_J = 125^\circ\text{C}$		--	--	100	
Drain-Source On-State Resistance <small>(Note 5)</small>	$V_{GS} = 10\text{V}, I_D = 50\text{A}$	$R_{DS(\text{on})}$	--	1.3	1.9	$\text{m}\Omega$
	$V_{GS} = 7\text{V}, I_D = 50\text{A}$		--	1.6	2.3	
Forward Transconductance <small>(Note 5)</small>	$V_{DS} = 10\text{V}, I_D = 12.5\text{A}$	g_{fs}	--	88	--	S
Dynamic <small>(Note 6)</small>						
Total Gate Charge	$V_{GS} = 7\text{V}, V_{DS} = 25\text{V}, I_D = 30\text{A}$	Q_g	--	64	96	nC
Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 25\text{V}, I_D = 30\text{A}$	Q_g	--	89	134	
Gate-Source Charge		Q_{gs}	--	28	56	
Gate-Drain Charge		Q_{gd}	--	16	32	
Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	6029	9044	pF
Output Capacitance		C_{oss}	--	1218	2436	
Reverse Transfer Capacitance		C_{rss}	--	47	94	
Gate Resistance	$f = 1.0\text{MHz}$	R_g	--	1.0	--	Ω
Switching <small>(Note 7)</small>						
Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 25\text{V}, I_D = 30\text{A}, R_G = 3.3\Omega$	$t_{d(on)}$	--	23	--	ns
Rise Time		t_r	--	76	--	
Turn-Off Delay Time		$t_{d(off)}$	--	52	--	
Fall Time		t_f	--	18	--	
Source-Drain Diode						
Diode Forward Voltage <small>(Note 5)</small>	$V_{GS} = 0\text{V}, I_S = 50\text{A}$	V_{SD}	--	--	1.1	V
Reverse Recovery Time	$I_S = 30\text{A},$ $dI/dt = 100\text{A}/\mu\text{s}$	t_{rr}	--	61	--	ns
Reverse Recovery Charge		Q_{rr}	--	98	--	nC

Notes:

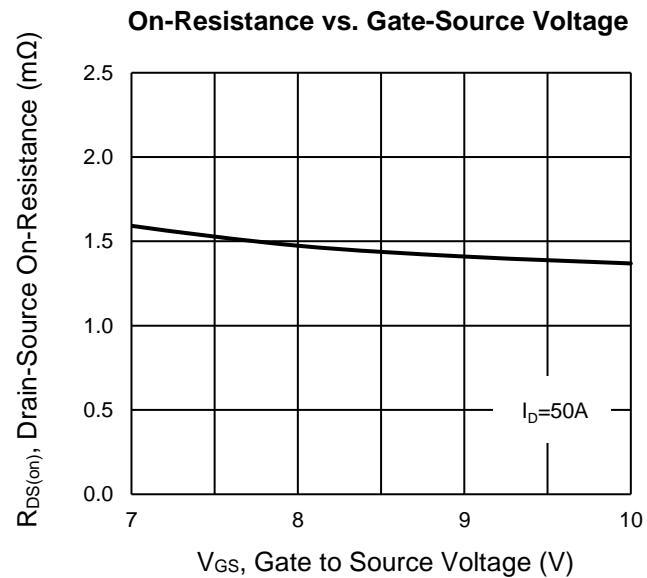
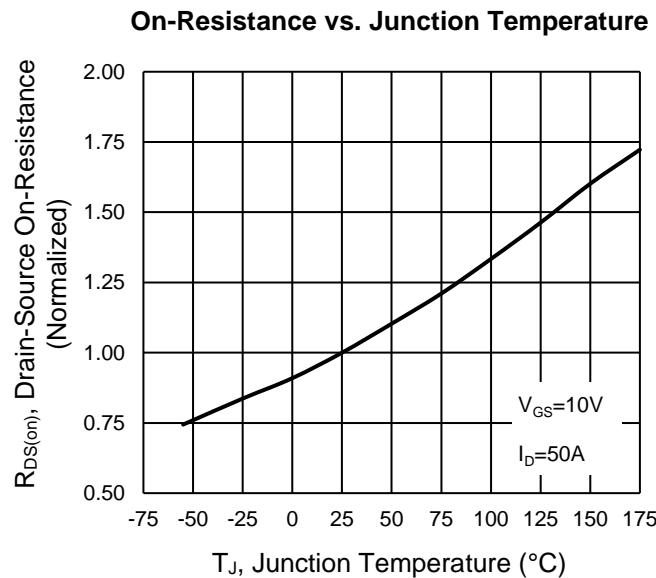
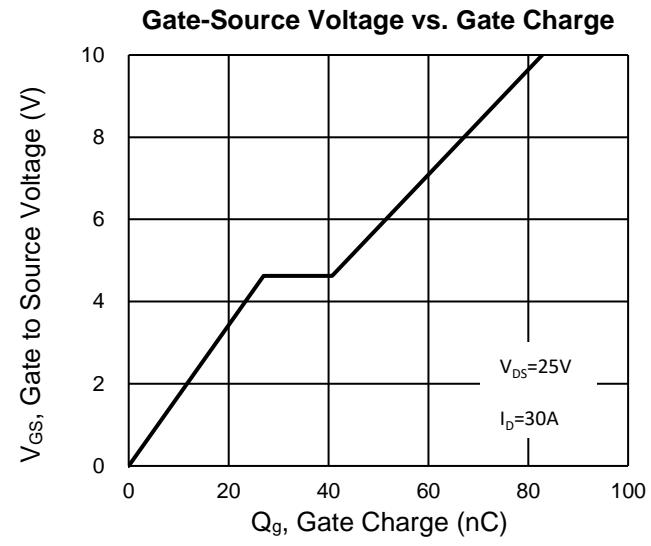
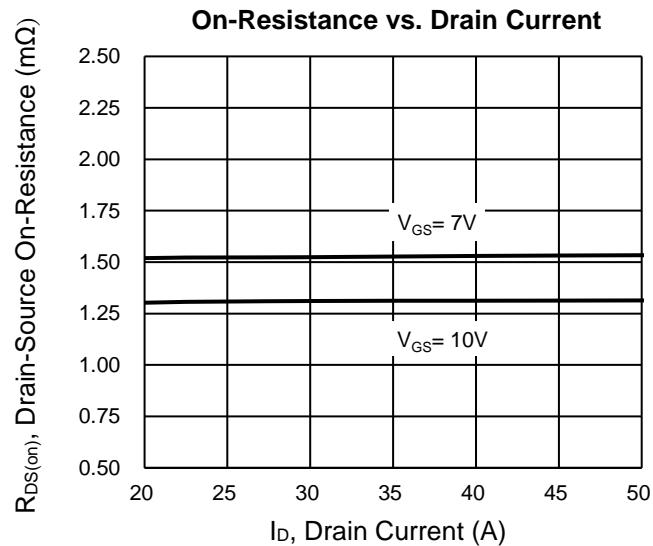
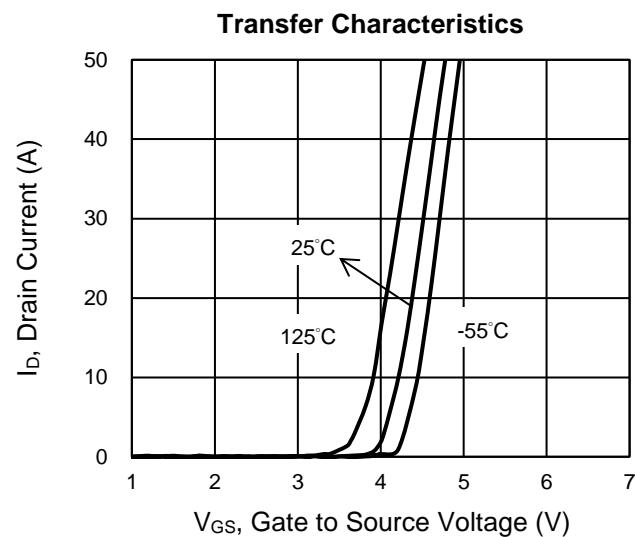
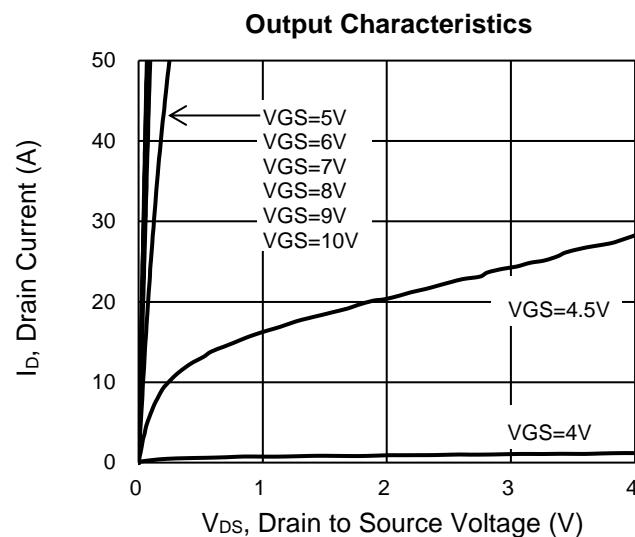
5. Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
6. Defined by design. Not subject to production test.
7. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TQM019NH04CR RLG	PDFN56U	2,500pcs / 13" Reel

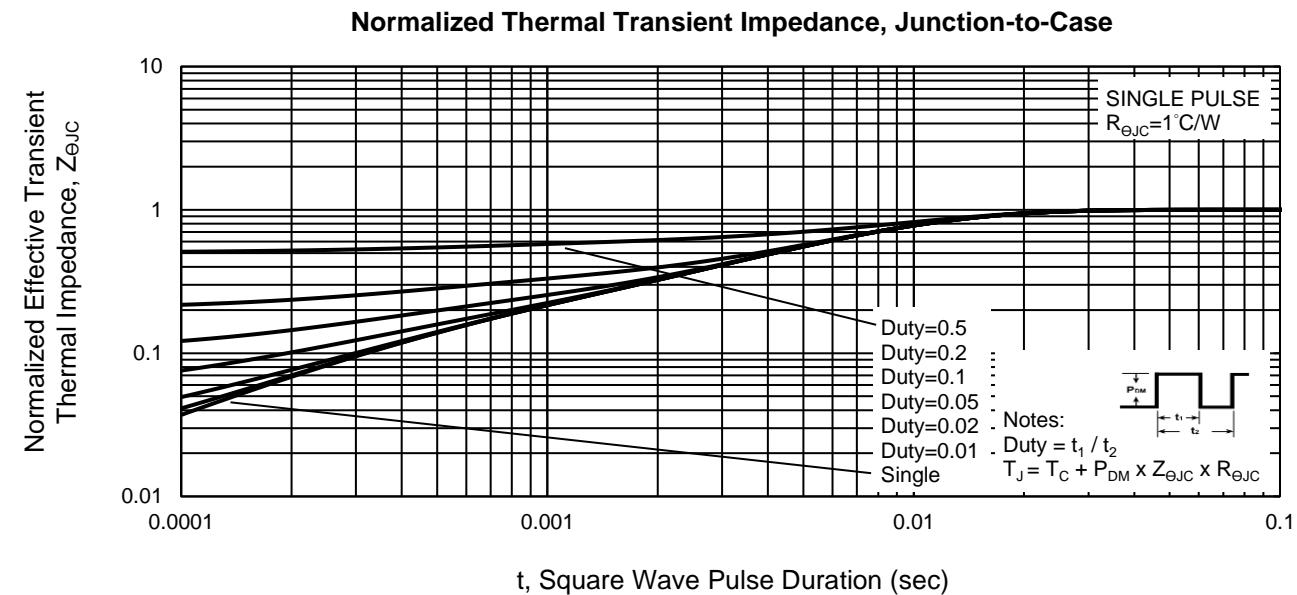
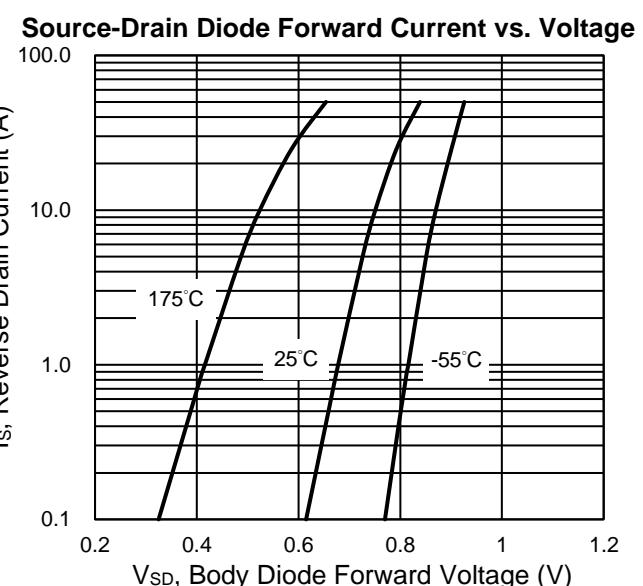
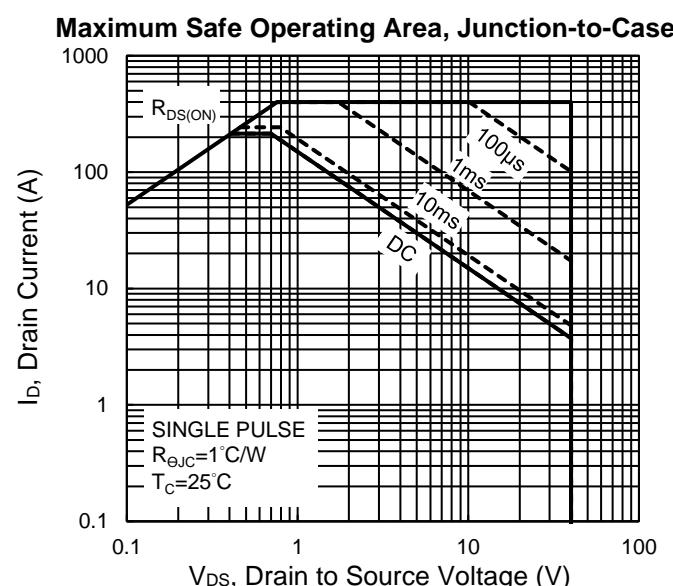
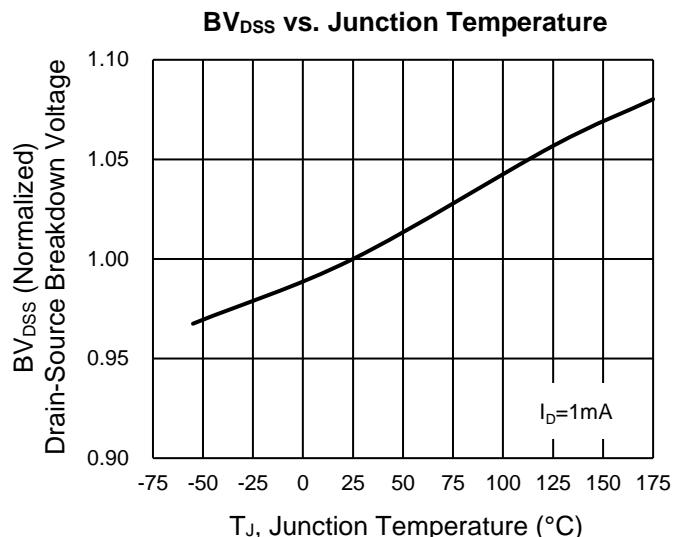
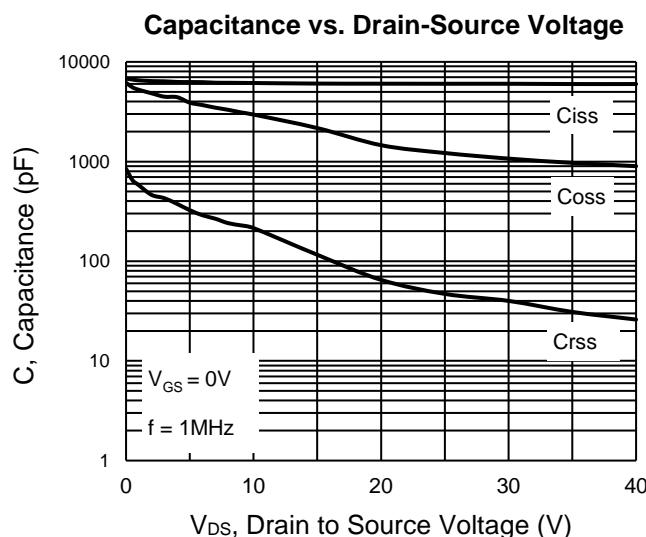
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)



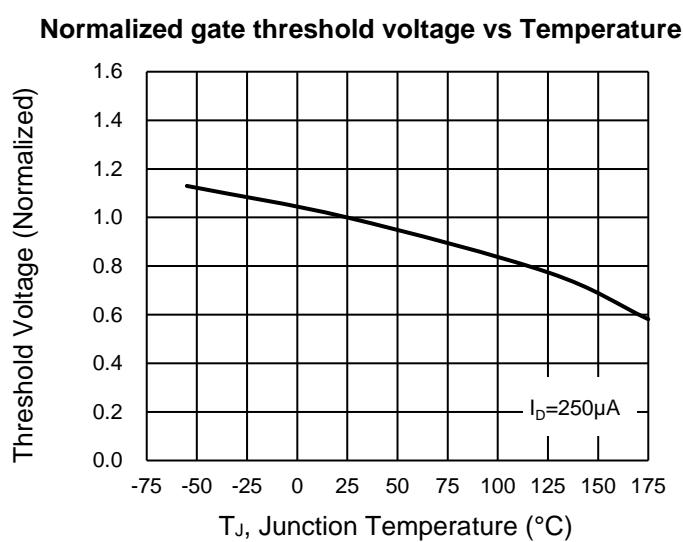
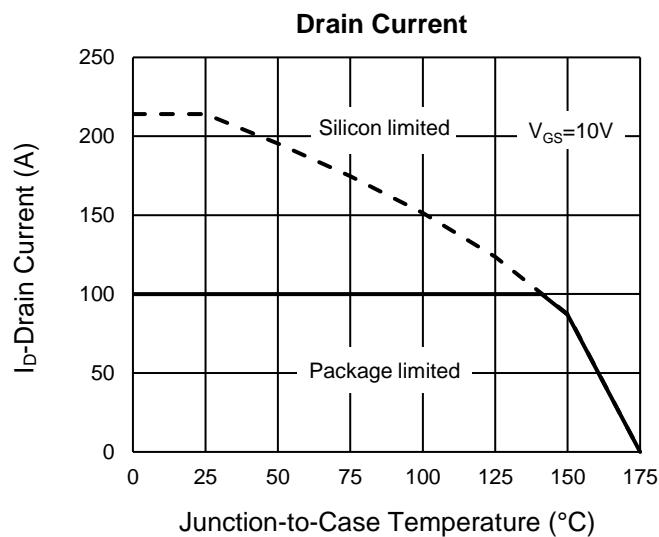
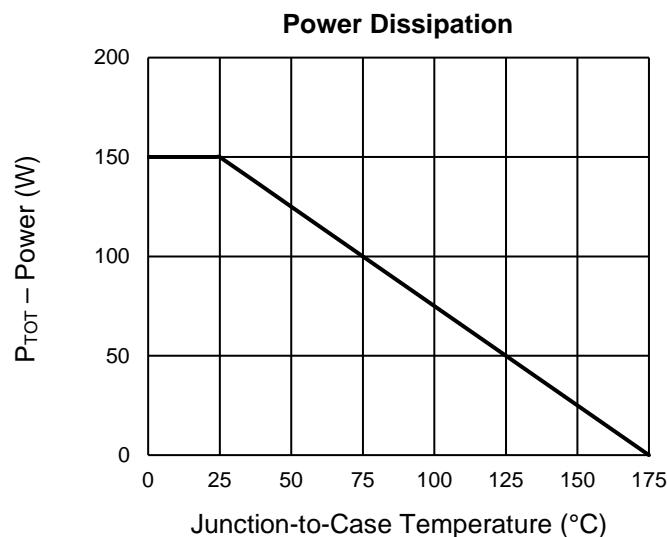
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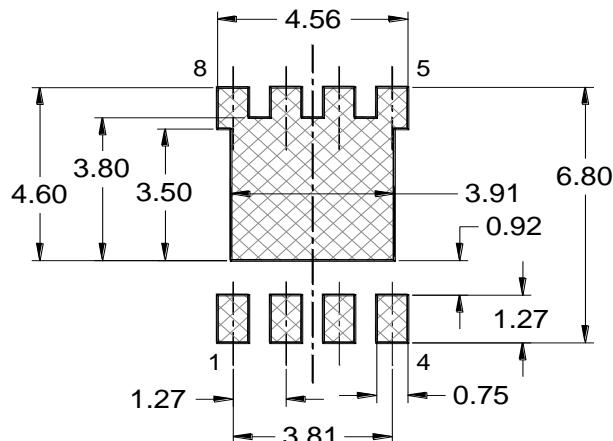
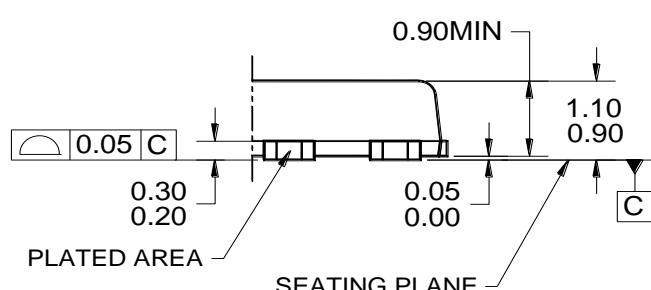
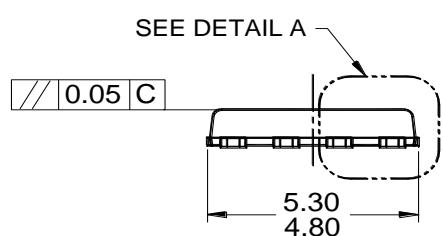
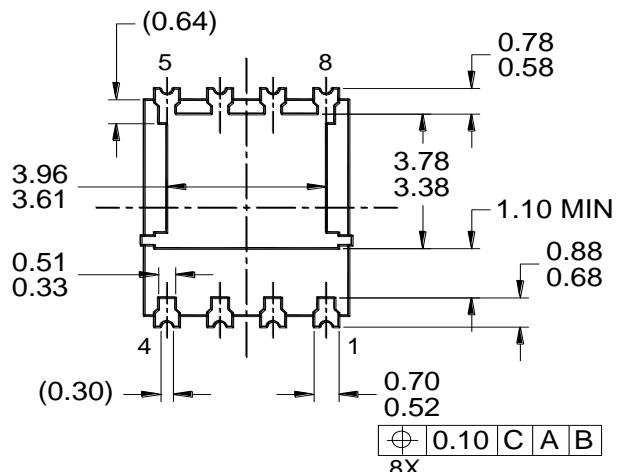
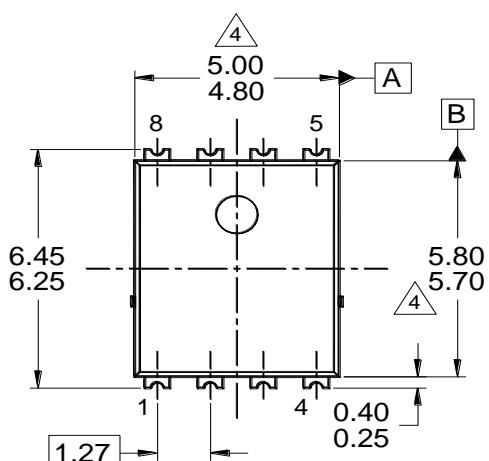
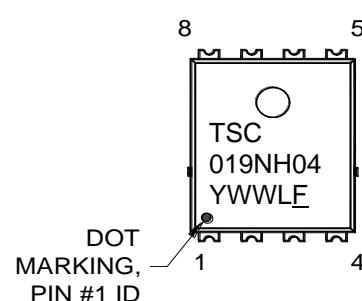


CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

PDFN56U

**SUGGESTED PAD LAYOUT
(REFERENCE ONLY)**


NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE:
JEITA ED-7500B, EIAJ SC-111BB.
-  MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-PDFN56U-023 REV B.

MARKING DIAGRAM

Y	= YEAR CODE
WW	= WEEK CODE (01~52)
L	= LOT CODE (1~9, A~Z)
F	= FACTORY CODE
-	= AEC-Q101 QUALIFIED

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